Switching (45V, 7.0A) **RSS070N05**

勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-34970699 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

Features

- 1) Built-in G-S Protection Diode.
- 2) Small and Surface Mount Package (SOP8).

Applications

Power switching, DC / DC converter, Inverter

Structure

Silicon N-channel MOS FET

Packaging dimensions

Package	Taping
Code	TB
Basic ordering unit(pieces)	2500

● Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit	
Drain-source voltage		V_{DSS}	45	V
Gate-source voltage		V_{GSS}	20	V
Drain current	Continuous	I_D	±7.0	Α
	Pulsed	I_{DP}	±28	Α *
Source current (Body diode)	Continuous	I _S	1.6	Α
	Pulsed	I_{SP}	28	Α *
Total power dissipation	P_{D}	2	W *2	
Chanel temperature	T_{ch}	150	°C	
Range of Storage temperature		T_{stg}	-55 to +150	°C

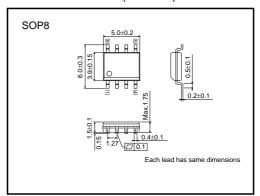
^{*1} PW \leq 10 μ s, Duty cycle \leq 1%

●Thermal resistance (Ta=25°C)

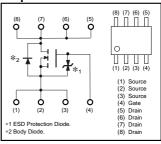
Parameter	Symbol	Limits	Unit
Chanel to ambient	R _{th(ch-a)}	62.5	°C/W *2

^{*2} Mounted on a ceramic board

●External dimensions (Unit : mm)



●Equivalent circuit



A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use.Use a protection circuit when the fixed voltage are exceeded.

^{*2} Mounted on a ceramic board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Gate-source leakage	I _{GSS}	_	_	10	μΑ	$V_{GS}=20V/V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	45	_	_	V	$I_D=1mA/V_{GS}=0V$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	V_{DS} =45V/ V_{GS} =0V
Gate threshold voltage	$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS}=10V/I_{D}=1mA$
Static drain-source on-state resistance		_	18	25	mΩ	$I_D=7A/V_{GS}=10V$
	R _{DS(on)} *	_	23	32		$I_D=7A/V_{GS}=4.5V$
		_	25	35		$I_D=7A/V_{GS}=4.0V$
Forward transfer admittance	Y _{fs} *	6.0	_	_	S	$V_{DS}=10V/I_{D}=7A$
Input capacitance	C _{iss}	_	1000	_	pF	V _{DS} =10V
Output capacitance	C _{oss}	_	230	_		V _{GS} =0V f=1MHz
Reverce transfer capacitance	C_{rss}	_	125	_	1	
Turn-on delay time	t _{d(on)} *	_	16	_	ns	V _{DD} =25V I _D =3.5A V _{GS} =10V
Rise time	t _r *	_	27	_		
Turn-off delay time	t _{d(off)} *	_	57	_		
Fall time	t _f *	_	21	_		$R_L=7.1\Omega/R_G=10\Omega$
Total gate charge	Q _g *	_	12.0	16.8	nC	$V_{DD}=25V/I_{D}=7 A$
Gate-source charge	Q _{gs} *	_	3.0	_		V _{GS} =5V
Gate-drain charge	Q _{gd} *	_	4.6	_		R_L =3.6 Ω/R_G =10 Ω

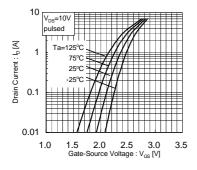
^{*} pulsed

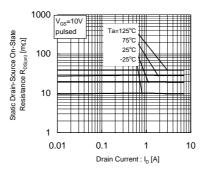
●Body diode characteristics (Source-Drain)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition
Forward voltage	V _{SD} *	_	_	1.2	V	$I_S=1.6A/V_{GS}=0V$

^{*} pulsed

Electrical characteristic curves





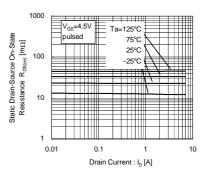
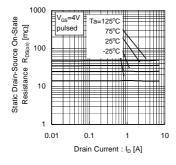


Fig.1 Typical Transfer Characteristics

Fig.2 Static Drain-Source On-State Resistance vs. Drain Current (1)

Fig.3 Static Drain-Source On-State Resistance vs. Drain Current (2)



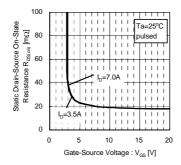


Fig.5 Static Drain-Source

On-State Resistance vs.

Gate-Source Voltage

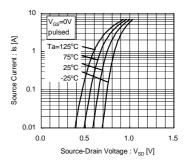


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current (3)

Ta=25°C

GS=0V

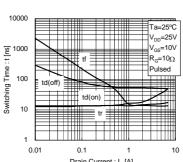


Fig.6 Source-Current vs. Source-Drain Voltage

Ta=25°C

9 8

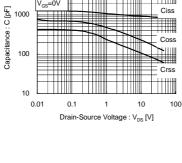
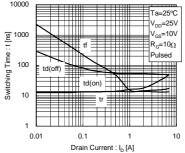


Fig.7 Typical capacitance vs.

Source-Drain Voltage

Ciss



Gate-Source Voltage: V_{GS}[V] 7 $R_G=10\Omega$ 6 Pulsed 5 4 3 2 1 0 0 10 15 20

Fig.8 Switching Characteristics

Fig.9 Dynamic Input Characteristics

Total Gate Charge : Qg [nC]

Measurement circuits

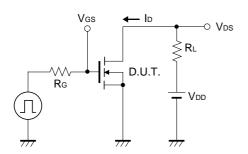


Fig.10 Switching Time Test Circuit

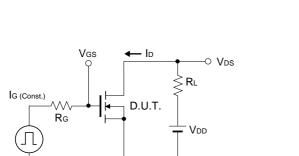


Fig.12 Gate Charge Test Circuit

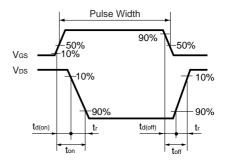


Fig.11 Switching Time Waveforms

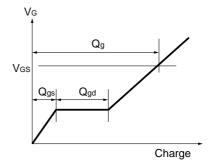


Fig.13 Gate Charge Waveform

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